



MATCHED DUAL NPN TRANSISTORS IN U-DFN2020-6

Features

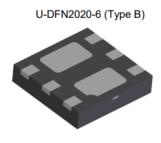
- BV_{CEO} > 120V
- I_C = 1A Continuous Current
- $R_{CE(sat)} = 240 m\Omega$
- 2% Matched Tolerance: $V_{BE(sat)}$ & $V_{BE(on)}$
- 4% Matched Tolerance: hFE
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

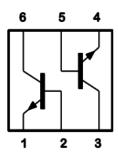
- Package: U-DFN2020-6
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)

Applications

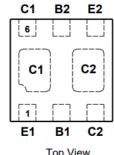
- Current mirrors
- Differential amplifiers
- Linear voltage regulators
- MOSFET drivers
- Load switches
- Power management
- Charging circuits



Bottom View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

Orderable Part Number	Package	Marking	Reel Size (inches)	Tana Width (mm)	Packing		
Orderable Part Nulliber	Package	Warking	Reel Size (Iliches)	rape widin (min)	Qty.	Carrier	
DSS4112FDB-7	U-DFN2020-6 (Type B)	2X9	7	8	3,000	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

U-DFN2020-6 (Type B)



2X9 = Product Type Marking Code Y = Year: 0 to 9 W = Week: A to Z: 1 to 26 Week; a to z: 27 to 52 Week; z Represents 52 and 53 Week

X = A to G: Internal Code

Date Code Key

Year	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035	2036
Code	5	6	7	8	9	0	1	2	3	4	5	6

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Green	Α	В	С	D	E	F	G

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	VcBo	150	V
Collector-Emitter Voltage	V _{CEO}	120	V
Emitter-Base Voltage	V _{EBO}	8	V
Continuous Collector Current	Ic	1	Α
Peak Collector Current	Ісм	1.5	А



Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 5)		0.42	
	(Note 6)		0.53	
Power Dissipation	(Note 7)	P _D	0.66	W
Fower Dissipation	(Note 8)		0.88	VV
	(Note 9)		0.85	
	(Note 10)		1.2	
	(Note 5)		295	
	(Note 6)		235	
Thermal Resistance, Junction to Ambient	(Note 7)	R _θ JA	190	°C/W
Thermal Nesistance, Junction to Ambient	(Note 8)		142	C/VV
	(Note 9)		147	
	(Note 10)		104	
Thermal Resistance, Junction to Case	(Note 5)	D	53	°C/W
Thermal Nesistance, Junction to Case	(Note 6)	R _θ JC	64	C/VV
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С
Electrostatic Discharge – Charge Device Model	ESD CDM	1000	V	IV

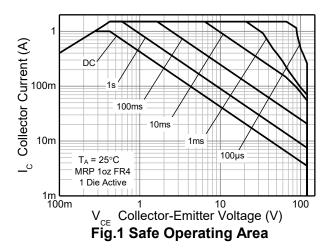
Notes:

- 5. For a device mounted with the exposed collector pad mounted on MRP 1oz copper single sided FR4 PCB, device is measured under still air conditions whilst operating in the steady state. Tested with one active die running.
- 6. Same as Note 5 but with two active die running.
- 7. For a device with each exposed collector pad mounted on 5mm × 5mm 1oz copper single sided FR4 PCB, device is measured under still air conditions whilst operating in the steady state. Tested with one active die running.
- 8. Same as Note 7 but with two active die running.
- 9. For a device with each exposed collector pad mounted on 10mm × 10mm 1oz copper single sided FR4 PCB, device is measured under still air conditions whilst operating in the steady state. Tested with one active die running.
- 10. Same as Note 9 but with two active die running.

 11. Refer to JEDEC specifications JESD22-A114, JESD22-A115 & JS-002.



Thermal Characteristics and Derating Information



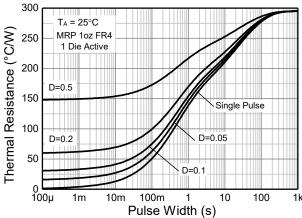


Fig.2 Transient Thermal Impedance

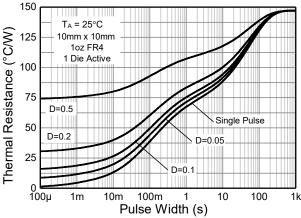


Fig.3 Transient Thermal Impedance

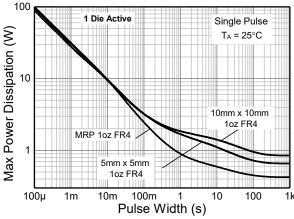


Fig.4 Pulse Power Dissipation

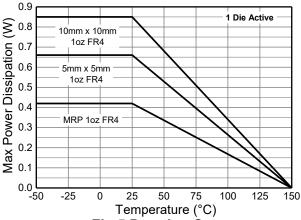


Fig.5 Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS			•	•	•	•
Collector-Base Breakdown Voltage	ВУсво	150	295	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BVceo	120	145	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	8	9.3	_	V	I _E = 100μA
Collector-Base Cutoff Current	1		1	100	nA	V _{CB} = 120V, I _E = 0
Collector-Base Cutoff Current	I _{CBO}		0.2	10	μΑ	V _{CB} = 120V, I _E = 0, T _J = +150°C
Emitter Cutoff Current	I _{EBO}	-	1	50	nA	V _{EB} = 7V
ON CHARACTERISTICS (Note 12)						_
DC Current Gain	hFE	250 300 80 30	415 410 130 44	600 —	_	Ic = 10mA, VcE = 2V Ic = 100mA, VcE = 2V Ic = 500mA, VcE = 2V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	66 175 113	120 260 220	mV	Ic = 1A, V _{CE} = 2V Ic = 500mA, I _B = 50mA Ic = 1A, I _B = 50mA Ic = 1A, I _B = 100mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	_	240	mΩ	Ic = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	0.82 0.84 0.87	1 1.1 1.1	V	Ic = 500mA, I _B = 50mA I _C = 1A, I _B = 50mA I _C = 1A, I _B = 100mA
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	750	900	mV	Ic = 500mA, VcE = 2V
MATCHING CHARACTERISTICS	. ,		I	I		
DC Current Gain Matching	hFE1/hFE2	-4%	_	+4%	_	I _C = 100mA, V _{CE} = 2V
Base-Emitter Turn-On Voltage Matching	VBE(on)1- VBE(on)2	-2%	_	+2%	_	Ic = 500mA, VcE = 2V
Collector-Emitter Saturation Voltage Matching	VCE(sat)1/ VCE(sat)2	-4%	_	+4%	_	I _C = 1A, I _B = 50mA
Base-Emitter Saturation Voltage Matching	V _{BE(sat)1} / V _{BE(sat)2}	-2%	_	+2%	_	Ic = 500mA, I _B = 50mA
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance	Cobo		6.75		pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	120	195	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Delay Time	t _d		33	_	ns	
Rise Time	t _r		374	_	ns	V _{CC} = 10V, I _C = 0.5A,
Storage Time	ts		837	_	ns	$I_{B1} = -I_{B2} = 25mA$
Fall Time	t _f	_	291	_	ns	

Note: 12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Timing Waveform

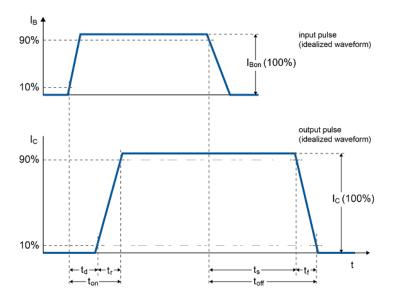


Fig.6 Timing Waveform



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

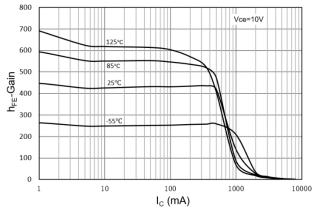


Fig.7 h_{FE} vs I_{C}

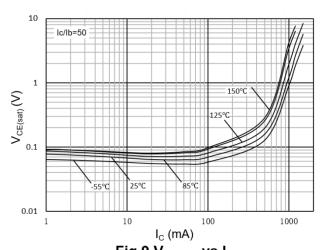
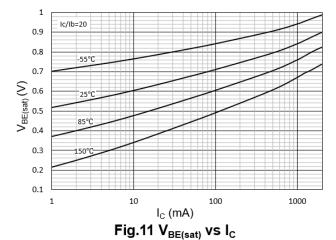


Fig.9 $V_{\text{CE(sat)}}$ vs I_{C}



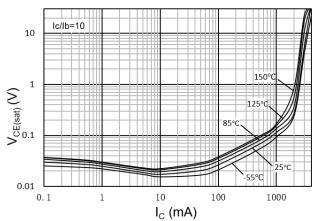
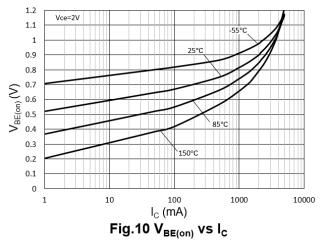


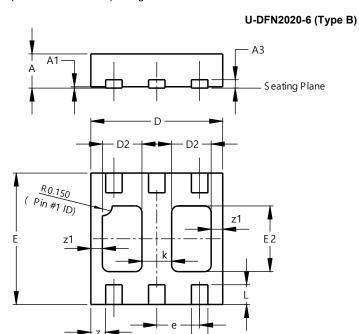
Fig.8 $V_{CE(sat)}$ vs I_{C}





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

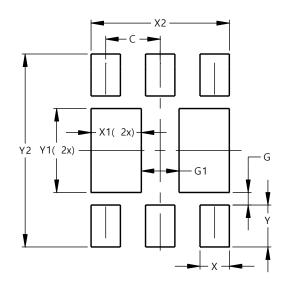


	U-DFN2020-6 Type B						
Dim	Min	Max	Тур				
Α	0.545	0.605	0.575				
A1	0.00	0.05	0.02				
A3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	0.50	0.70	0.60				
е	-	-	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
k	-	-	0.45				
L	0.25	0.35	0.30				
Z	-	-	0.225				
z1	-	-	0.175				
All	Dimens	ions in	mm				

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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